

2SD468

Silicon NPN Epitaxial

REJ03G0766-0200 (Previous ADE-208-1135) Rev.2.00 Aug.10.2005

Application

- Low frequency power amplifier
- Complementary pair with 2SB562

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Collector to base voltage	V _{CBO}	25	V	
Collector to emitter voltage	V_{CEO}	20	V	
Emitter to base voltage	V _{EBO}	5	V	
Collector current	I _C	1.0	A	
Collector peak current	i _{C(peak)}	1.5	Α	
Collector power dissipation	Pc	0.9	W	
Junction temperature	Tj	150	O C	
Storage temperature	Tstg	-55 to +150	°C	

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

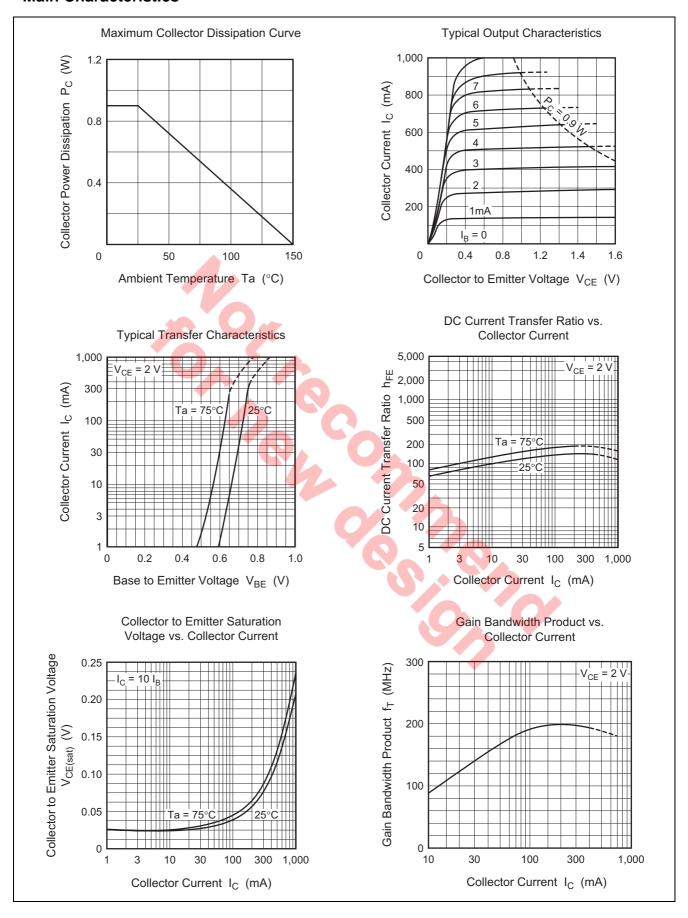
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	25	_	_	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	_	_	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I _{CBO}	_	_	1.0	μΑ	$V_{CB} = 20 \text{ V}, I_{E} = 0$
DC current transfer ratio	h _{FE} *1	85	_	240		$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	_	0.2	0.5	V	$I_C = 0.8 \text{ A}, I_B = 0.08 \text{ A}^{*2}$
Base to emitter voltage	V_{BE}	_	0.79	1.0	V	$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}^{*2}$
Gain bandwidth product	f⊤	_	190	_	MHz	$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}^{*2}$
Collector output capacitance	Cob	_	22	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

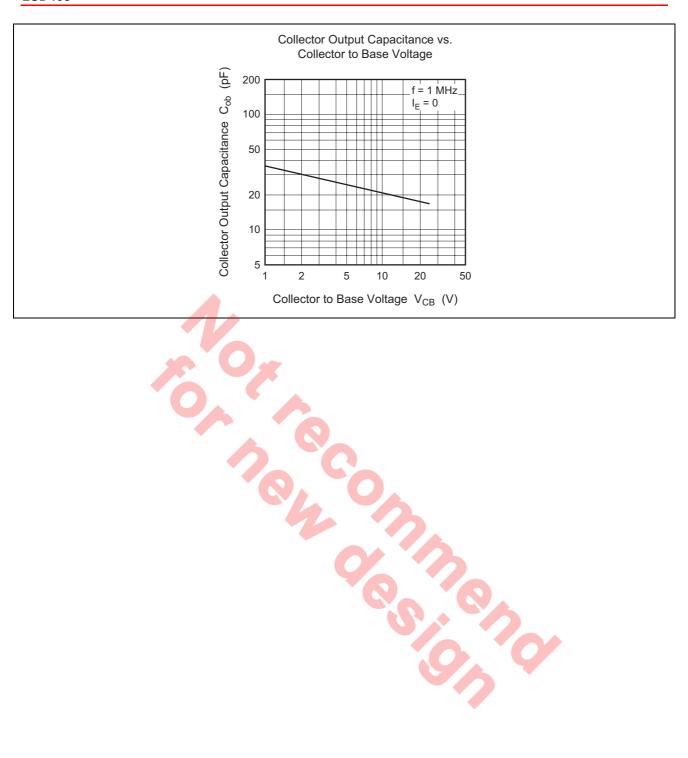
Notes: 1. The 2SD468 is grouped by h_{FE} as follows.

2. Pulse test

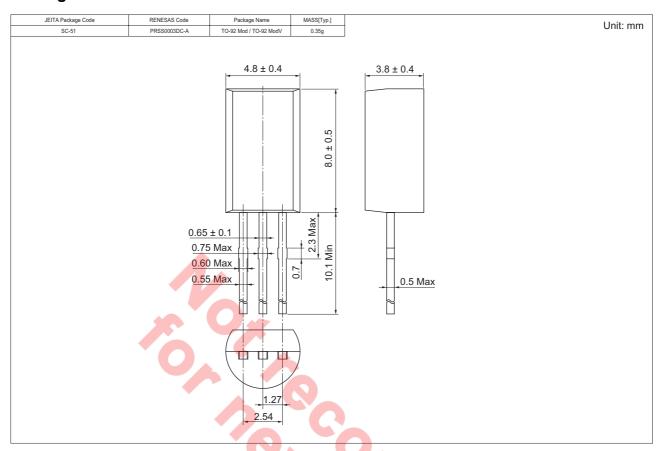
В	С	
85 to170	120 to 240	$A \rightarrow$
		A U
	,	

Main Characteristics





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SD468BTZ-E	2500	Hold Box, Radial Taping
2SD468CTZ-E		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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